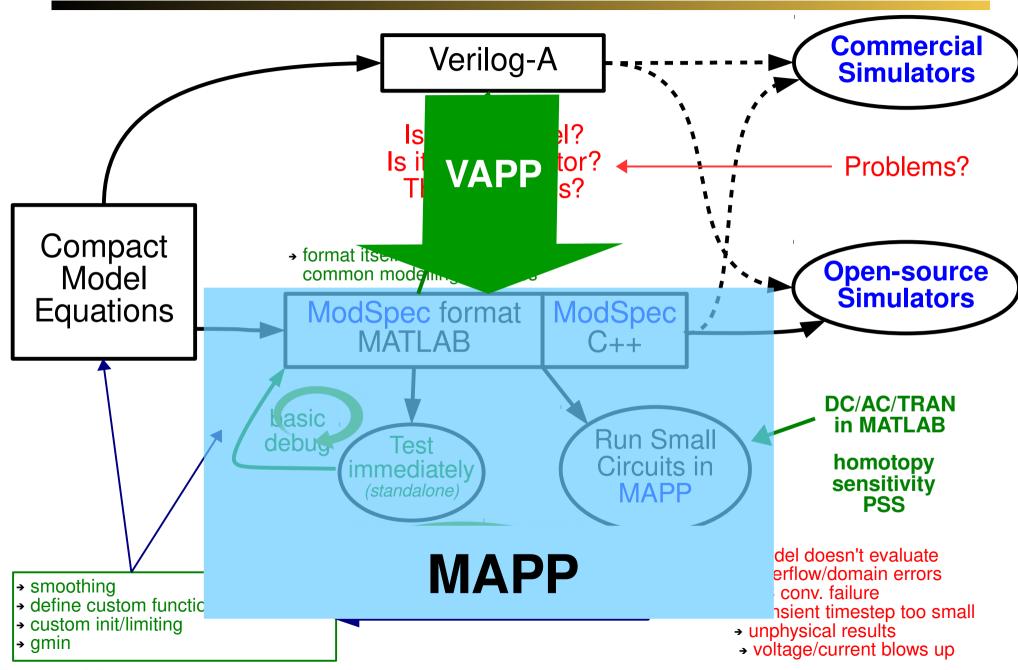
Berkeley MAPP and VAPP

(Model and Algorithm Prototyping Platform)
(Verilog-A Parser and Processor)

Tianshi Wang, A. Gokcen Mahmutoglu, Karthik Aadithya*, Archit Gupta and Jaijeet Roychowdhury

EECS Department, University of California, Berkeley *Sandia National Laboratories

Compact Model Development



T. Wang, UC Berkeley

```
function MOD = diodeCapacitor_ModSpec_wrapper()
    % ModSpec description of an ideal diode in parallel with a capacitor
        MOD = ee_model():
        MOD = add_to_ee_model(MOD, 'external_nodes', {'p', 'n'});
MOD = add_to_ee_model(MOD, 'explicit_outs', {'ipn'});
MOD = add_to_ee_model(MOD, 'parms', {'C',2e-12, 'Is',1e-12});
MOD = add_to_ee_model(MOD, 'f', @f);
                                                                         2, 'Is',1e-12, 'VT',0.025})
        MOD = add_to_ee_model(MOD, 'q', @q)
 9 end
11 function out = f(S)
          v2struct(S)
          out = Is*(exp(vpn/VT)-1)
13
14 end
15
16 function out = q(S)
         v2struct(S):
          out = C=vpn
19 end
diodeCapacitor_ModSpec_wrapper.m" 19L, 548C written
                                                                                                          A11
                                                       \vec{z} = \frac{d}{dt} \vec{q_e}(\vec{x}, \vec{y}) + \vec{f_e}(\vec{x}, \vec{y}, \vec{u})
MOD.terminals
MOD.parms
MOD explicit outs
                                         ipn
MOD.f: function handle
MOD.q: function handle
                                                          \vec{0} = \frac{d}{dt}\vec{q}_i(\vec{x}, \vec{y}) + \vec{f}_i(\vec{x}, \vec{y}, \vec{u})
```

Executable & debuggable standalone

Easily & directly usable by any simulator

MOD.terminals
MOD.parms
MOD.explicit_outs
MOD.f: function handle
MOD.q: function handle

Easy to examine/write by hand

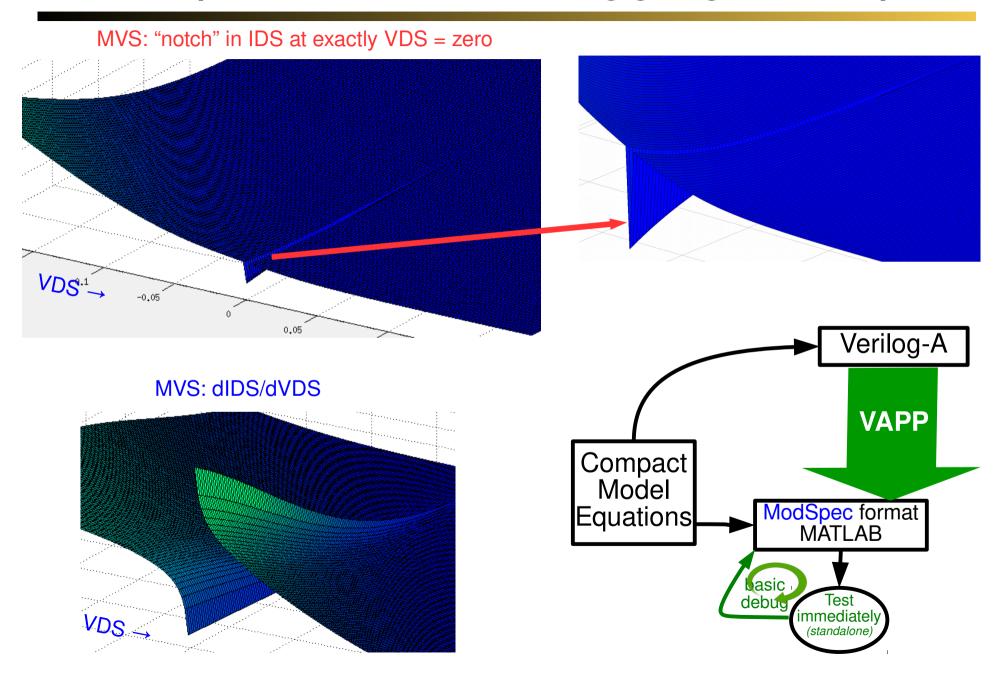
Supports every analysis DC/AC/tr/PSS General: any device in any physical domain

Mathematically well defined, modular

$$\vec{z} = \frac{d}{dt}\vec{q}_e(\vec{x}, \vec{y}) + \vec{f}_e(\vec{x}, \vec{y}, \vec{u})$$

$$\vec{0} = \frac{d}{dt}\vec{q}_i(\vec{x}, \vec{y}) + \vec{f}_i(\vec{x}, \vec{y}, \vec{u})$$

ModSpec: Model Debugging Example



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Easy to examine/write by hand

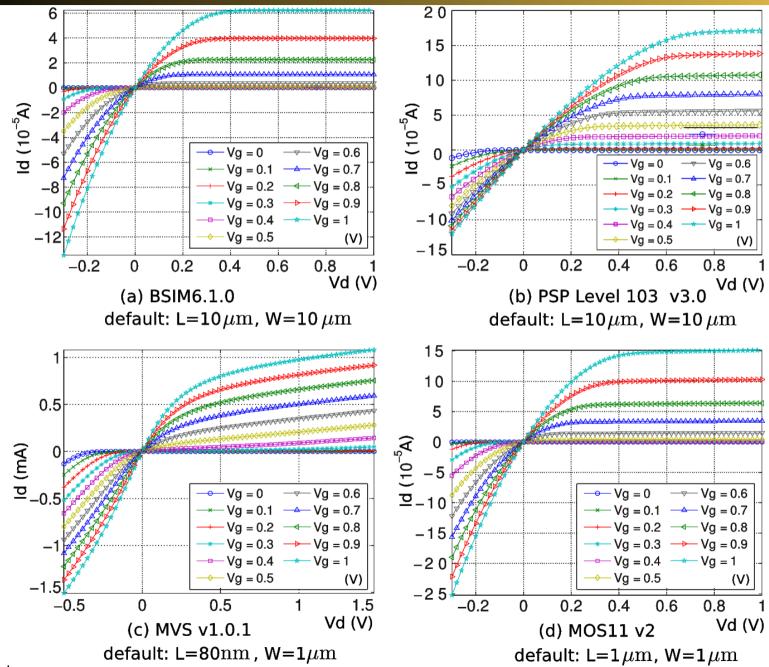
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$$\vec{z} = \frac{d}{dt}\vec{q}_e(\vec{x}, \vec{y}) + \vec{f}_e(\vec{x}, \vec{y}, \vec{u})$$

$$\vec{0} = \frac{d}{dt}\vec{q}_i(\vec{x}, \vec{y}) + \vec{f}_i(\vec{x}, \vec{y}, \vec{u})$$

MAPP: Compact Model Prototyping



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MOD.parms
MOD.explicit_outs
MOD.f: function handle
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Easy to examine/write by hand

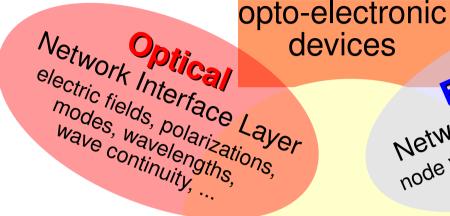
Supports every analysis DC/AC/tr/PSS General: any device in any physical domain

Mathematically well defined, modular

$$\vec{z} = \frac{d}{dt}\vec{q}_e(\vec{x}, \vec{y}) + \vec{f}_e(\vec{x}, \vec{y}, \vec{u})$$

$$\vec{0} = \frac{d}{dt}\vec{q}_i(\vec{x}, \vec{y}) + \vec{f}_i(\vec{x}, \vec{y}, \vec{u})$$

ModSpec: Multiphysics Support



Network Interface Layer node voltages, branch currents,

Mechanical NIL

ModSpec Core (Equations)

Thermal NIL

Spintronic NIL

Biochemical NIL

MOD.terminals MOD.parms MOD explicit outs MOD.f: function handle MOD.q: function handle

$$\vec{z} = \frac{d}{dt}\vec{q}_e(\vec{x}, \vec{y}) + \vec{f}_e(\vec{x}, \vec{y}, \vec{u})$$

$$\vec{0} = \frac{d}{dt}\vec{q}_i(\vec{x}, \vec{y}) + \vec{f}_i(\vec{x}, \vec{y}, \vec{u})$$

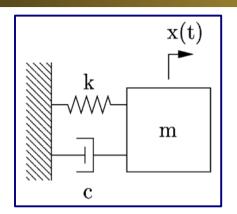
Multiphysics Systems

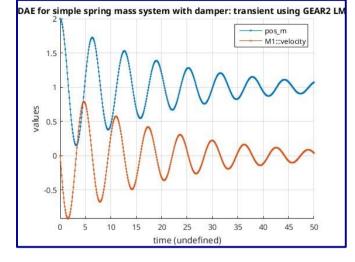
potential/flow systems:

kinematic NIL:

"flow": force

"potential": position





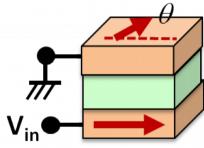
magnetic NIL:
"flow": magnetic flux

"potential": magnetomotive force

thermal NIL:

"flow": power flow

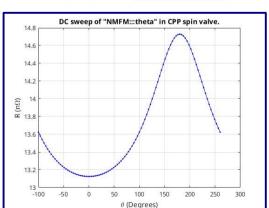
"potential": temperature



Spintronic systems:

vectorized spin currents vectorized spin voltages

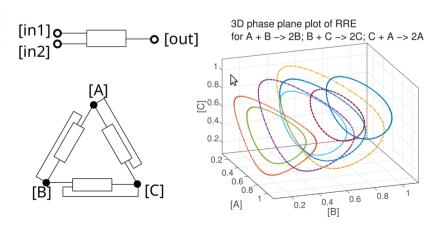
Kerem Yunus Camsari; Samiran Ganguly; Supriyo Datta (2013), "Modular Spintronics Library," https://nanohub.org/resources/17831.



Chemical reaction networks

rates and concentrations

"KCLs" at nodes have d/dt terms



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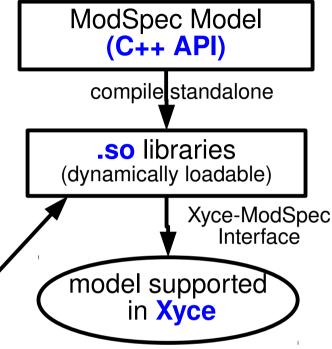
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$$\vec{0} = \frac{d}{dt}\vec{q}_i(\vec{x}, \vec{y}) + \vec{f}_i(\vec{x}, \vec{y}, \vec{u})$$

Glimpse: ModSpec Model in Xyce

```
1 *** Test-bench for generting dc response of an inverter
 3 *** Creat sub-circuit for the inverter
  .subckt inverter Vin Vout Vvdd Vand
  yModSpec Device X1 Vvdd Vin Vout Vvdd: MVSmod; type=-1 W=1.0e-4
      Lgdr=32e-7 dLg=8e-7 Cg=2.57e-6 beta=1.78-a1pha=3.5 Tjun=300
      Cif = 1.38e-12 Cof=1.47e-12 phib=1.2 damma=0.1 mc=0.2
      CTM select=1 Rs0=100 Rd0 = 100 \text{ n0}=1.68 \text{ nd}=0.1 \text{ vxo}=7542204
      mu=165 Vt0=0.5535 delta=0.15
10
11
12 vModSpec Device X0 Vout Vin Vand Vand MVSmod type=1 W=1e-4
13
      Lgdr=32e-7 dLg=9e-7 Cg=2.57e-6 beta=1.8 alpha=3.5 Tjun=300
14
      Cif=1.38e-12 Cof=1.47e-12 phib=1.2 gamma=0.1 mc=0.2
      CTM select=1 Rs0=100 Rd0=100 n0=1.68 nd=0.1 vxo=1.2e7
15
16
      mu=200 Vt0=0.4 delta=0.15
                                     .model line
17
18 .model MVSmod MODSPEC DEVICE SONAME=MVS ModSpec Element.sc
19
20 .ends
                model's name
                                     model parameter:
21
                                     name of .so library
22 *** circuit lavout
23 Vsup sup 0 1
24 Vin in 0 0
25 Vsource source 0 0
26 X2 in out sup 0 inverter
27
                            Xyce netlist for inverter
28 *** simulation
29 .dc Vin 0 1 0.01 (using MVS ModSpec/C++ model)
30
31 .print dc V(in) V(out)
32 *** END
33 .end
```



Updates in the last year

- limiting correction
- composite parameters
- works in Xyce 6.5

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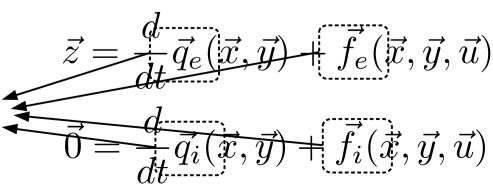
Differential Algebraic Equations

STEAM: Fast, Accurate Table-Based Models

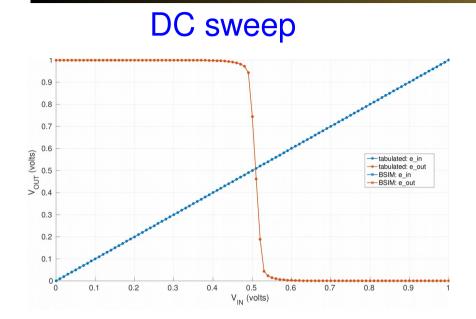
- Compact model using only tabulated i-v, q-v data?
 - » previous table-based attempts: important details unclear, poor accuracy, low speedup
 - » our goal: can we speed up existing compact models?
- Our approach: STEAM
 - » tabulate ModSpec functions fe, fi, qe, qi (one time cost)
 - » device eval: multi-dimensional cubic spline interpolation
- Initial results
 - » 150x eval speedup for BSIM3 (6-15x tran/DC)
 - » relative error as low as you like: eg, 10⁻⁴
 - but memory requirements grow with accuracy

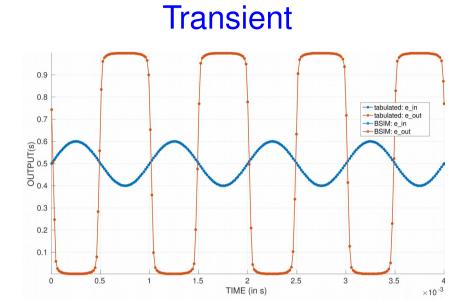
replace with "lookup" tables

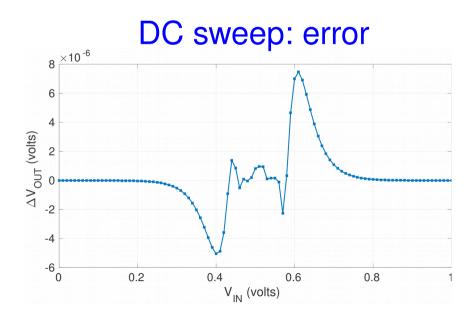
implementation details: multi-dimensional splines, passive extrapolation

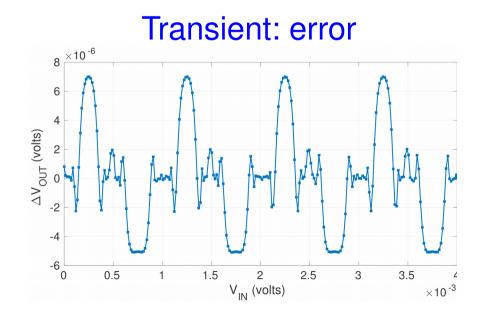


BSIM3 Inverter: STEAM vs Original









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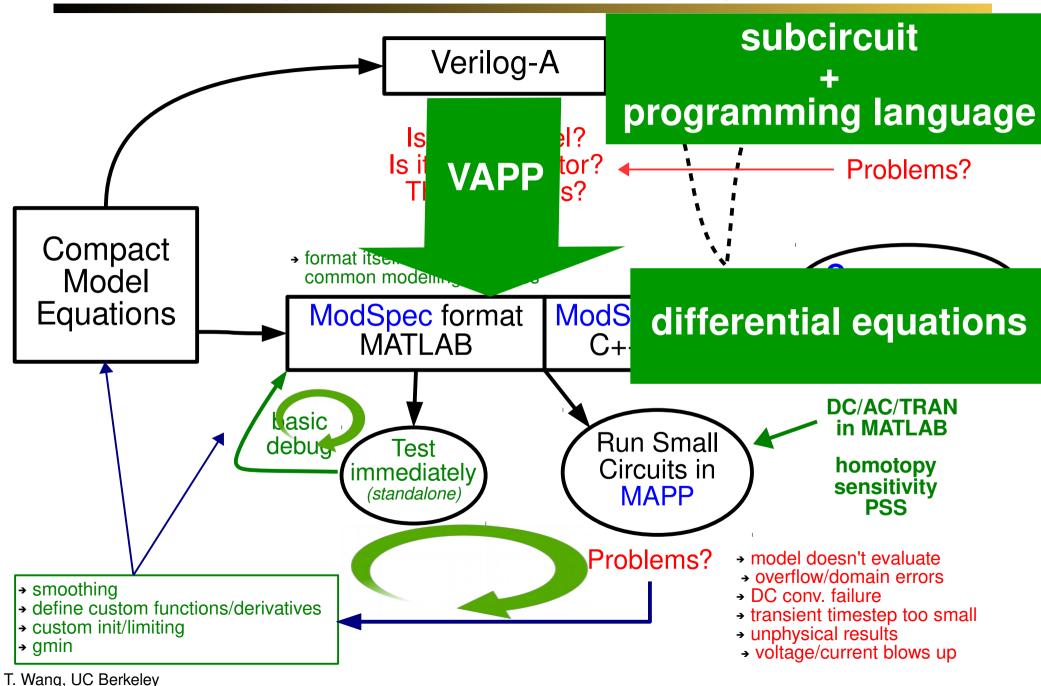
$$\vec{z} = \frac{d}{dt}\vec{q}_e(\vec{x}, \vec{y}) + \vec{f}_e(\vec{x}, \vec{y}, \vec{u})$$

$$\vec{0} = \frac{d}{dt}\vec{q}_i(\vec{x}, \vec{y}) + \vec{f}_i(\vec{x}, \vec{y}, \vec{u})$$

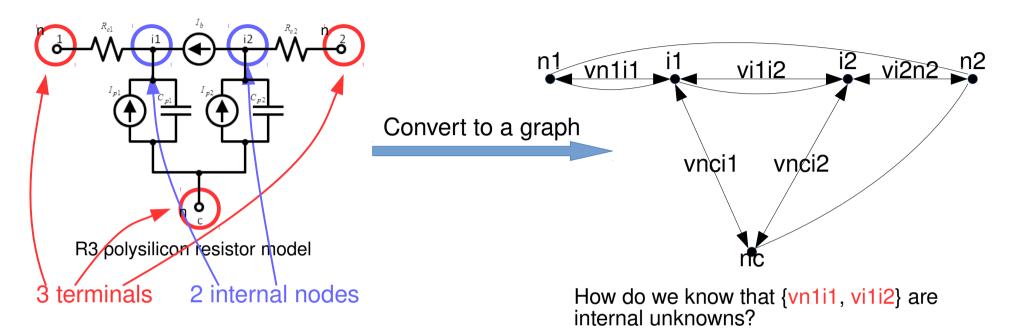
Differential Algebraic Equations

. . .

Compact Model Development



VAPP: New Graph Based Core



And {vnci1, vnci2} dependent voltages?

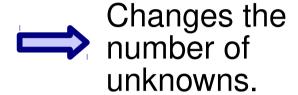
Algorithm:

- Construct a spanning tree (ST)
- Designate branches in the ST as independent voltages
- Remaining branches are independent currents
- Construct loop and cutset matrices
- Express dependent quantities in terms of independent ones

VAPP: What Is Still Lacking?

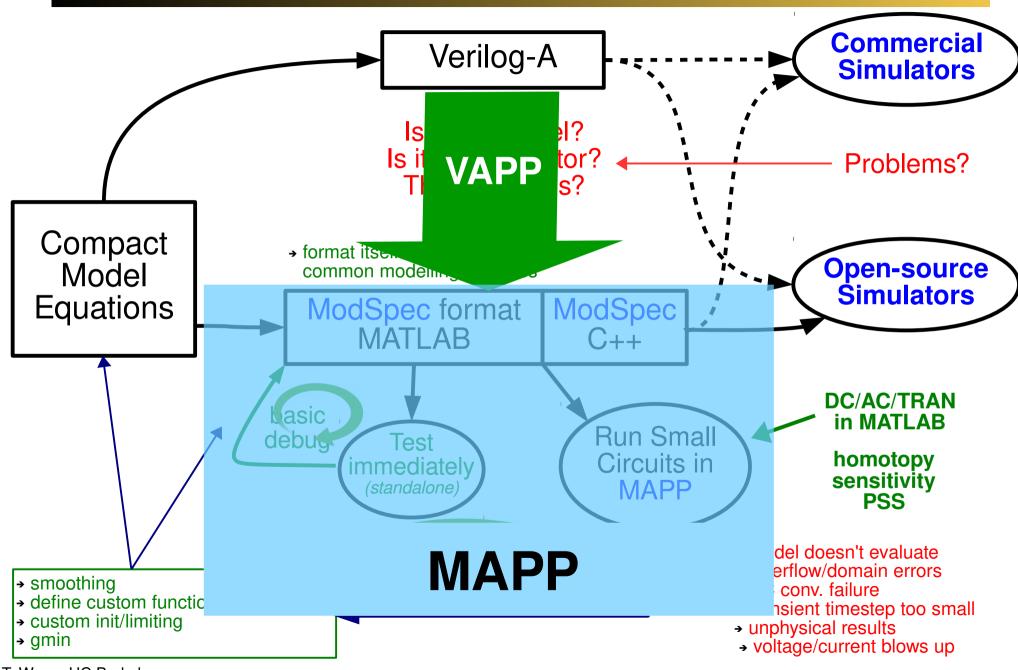
•Node collapse:

```
if (rdsmod == 0)
  begin
    V(source, sourcep) <+ 0;
    V(drainp, drain) <+ 0;
  end
else
  begin
    I(drain, drainp) <+ type * gdtot * vded;
    I(source, sourcep) <+ type * gstot * vses;
  end</pre>
```



- •Separate networks (graphs) for different disciplines. E.g., thermal, magnetic,...
 - Important for self heating.
- •Support for noise functions in MAPP. E.g., white_noise, flicker_noise

Compact Model Development



T. Wang, UC Berkeley

Memristive Devices & Applications

devices

UMich, Stanford, HP, HRL Labs, Micron, Crossbar, Samsung, ...



applications

- nonvolatile memories
- FPAAs
- neuromorphic circuits
- oscillators

Knowm





Compact Models

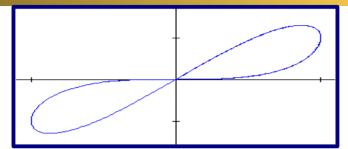
- Linear/nonlinear ion drift models
 Biolek (2009), Joglekar (2009),
 Prodromes to the works in DC
 - UMich RRAM model (2011)
- TEAM model (2012) Verilog-A problems
- Simmons tunneling barrier model (2013)
- Yakopcic model (2013)
- Stanford/ASU RRAM model (2014)
- Knowm "probabilistic" model (2015)

idt(), \$bound_step,
\$abstime, @initial_step,
\$rdist_normal, ...

T. Wang, UC Berkeley

Challenges in Memristor Modelling

- hysteresis
 - internal state variable



- model internal unks in Verilog-A
 - use potentials/flows
- upper/lower bounds of internal unks
 - -filament length, tunneling tap size
 - clipping functions
- smoothness, continuity, finite precision issues, ...
 - use smooth functions, safe functions
 - -GMIN
 - scaling of unks/eqns
 - SPICE-compatible limiting function (the only smooth one)

How to Model Hysteresis Properly

Template:

$$ipn = f_1 (vpn, s)$$

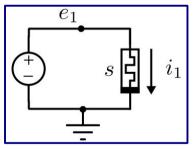
$$\frac{d}{dt}\mathbf{s} = f_2\left(\mathbf{vpn}, \ \mathbf{s}\right)$$

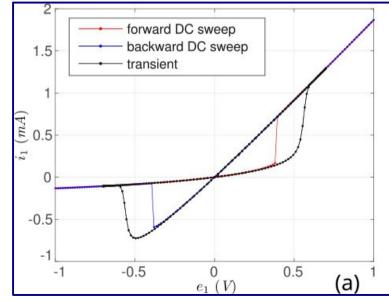
ModSpec:

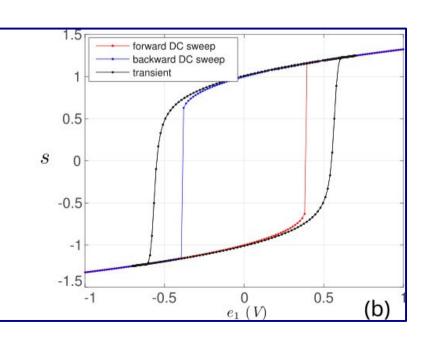
$$\mathbf{ipn} = \frac{d}{dt} \underline{q_e \, (\mathbf{vpn}, \, \mathbf{s})} + \underline{f_e \, (\mathbf{vpn}, \, \mathbf{s})}$$

$$0 = \frac{d}{dt} \underline{q_i \, (\mathbf{vpn}, \, \mathbf{s})} + \underline{f_i \, (\mathbf{vpn}, \, \mathbf{s})}$$

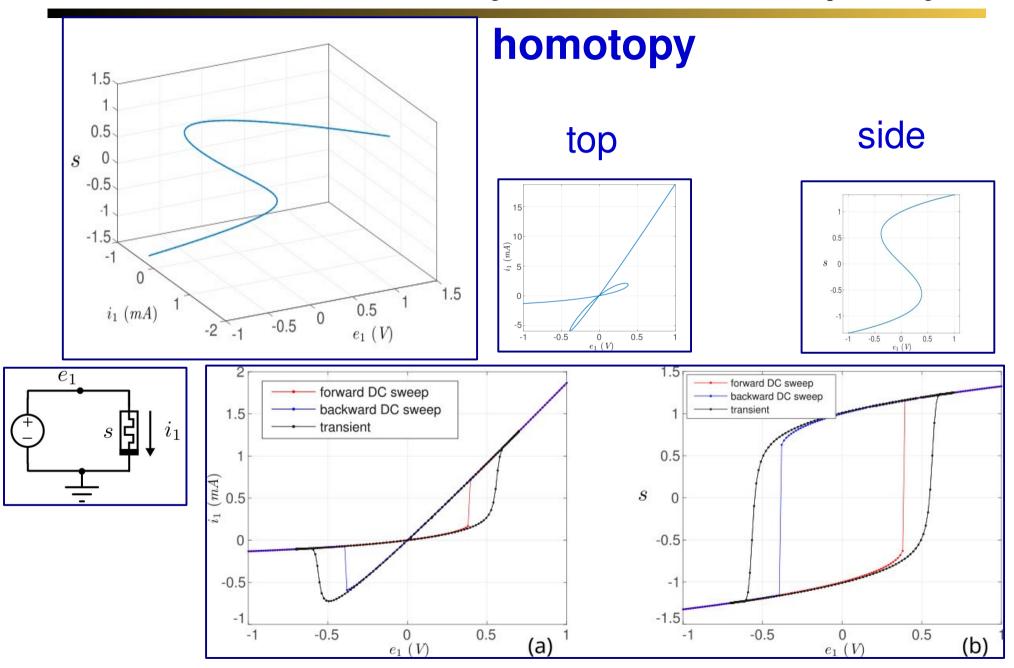
$$-\mathbf{s}$$







How to Model Hysteresis Properly



Memristor Models

$$\frac{d}{dt}\mathbf{s} = f_2\left(\mathbf{vpn}, \ \mathbf{s}\right)$$

Available f2:

linear ion drift

$$f_2 = \mu_v \cdot R_{on} \cdot f_1(\mathbf{vpn}, s)$$

nonlinear ion drift

$$f_2 = a \cdot \mathbf{vpn}^m$$

Simmons tunnelling barrier

$$f_2 = \begin{cases} c_{off} \cdot \sinh(\frac{i}{i_{off}}) \cdot \exp(-\exp(\frac{s - a_{off}}{w_c} - \frac{i}{b}) - \frac{s}{w_c}), & \text{if } i \ge 0\\ c_{on} \cdot \sinh(\frac{i}{i_{on}}) \cdot \exp(-\exp(\frac{a_{on} - s}{w_c} + \frac{i}{b}) - \frac{s}{w_c}), & \text{otherwise,} \end{cases}$$

- TEAM model
- Yakopcic model

Stanford/ASU
$$f_2 = -v_0 \cdot \exp(-\frac{E_a}{V_T}) \cdot \sinh(\frac{\mathbf{vpn} \cdot \gamma \cdot a_0}{t_{ox} \cdot V_T})$$

$ipn = f_1(vpn, s)$

Available f1:

$$f_1 = (R_{on} \cdot s + R_{off} \cdot (1 - s))^{-1} \cdot \mathbf{vpn}$$

$$f_1 = \frac{1}{R_{on}} \cdot e^{-\lambda \cdot (1-s)} \cdot \mathbf{vpn}$$

$$f_1 = s^n \cdot \beta \cdot \sinh(\alpha \cdot \mathbf{vpn}) + \chi \cdot (\exp(\gamma \cdot) - 1)$$

$$f_{2} = \begin{cases} c_{off} \cdot \sinh(\frac{i}{i_{off}}) \cdot \exp(-\exp(\frac{s - a_{off}}{w_{c}} - \frac{i}{b}) - \frac{s}{w_{c}}), & \text{if } i \geq 0 \\ c_{on} \cdot \sinh(\frac{i}{i_{on}}) \cdot \exp(-\exp(\frac{a_{on} - s}{w_{c}} + \frac{i}{b}) - \frac{s}{w_{c}}), & \text{otherwise,} \end{cases}$$

$$\mathbf{f}_{1} = \begin{cases} A_{1} \cdot s \cdot \sinh(B \cdot \mathbf{vpn}), & \text{if } \mathbf{vpn} \geq \mathbf{0} \\ A_{2} \cdot s \cdot \sinh(B \cdot \mathbf{vpn}), & \text{otherwise.} \end{cases}$$

$$f_1 = I_0 \cdot e^{-\mathbf{Gap}/g0} \cdot \sinh(\mathbf{vpn}/V_0)$$

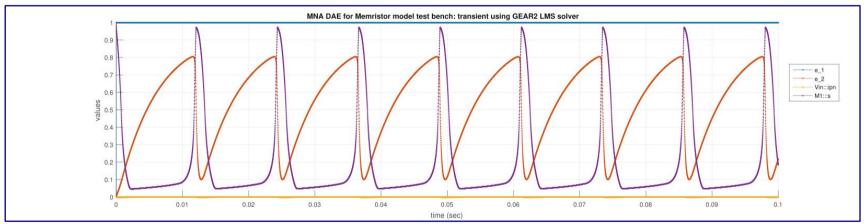
$$\mathbf{Gap} = s \cdot minGap + (1 - s) \cdot maxGap.$$

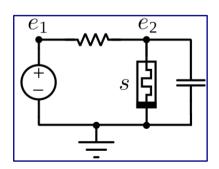
- set up boundary
- fix f2 flat regions
- smooth, safe funcs, scaling, etc.

Memristor Models

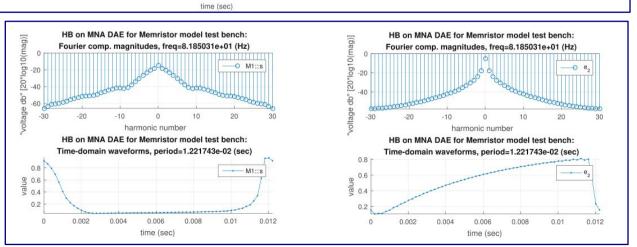
A collection of 30 models:

- all smooth, all well posed
- not just RRAM, but general memristive devices
- not just bipolar, but unipolar
- not just DC, AC, TRAN, but homotopy, PSS, ...



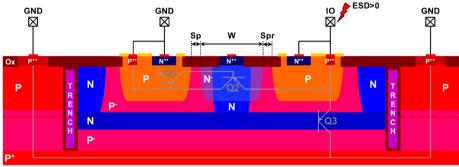


PSS using HB

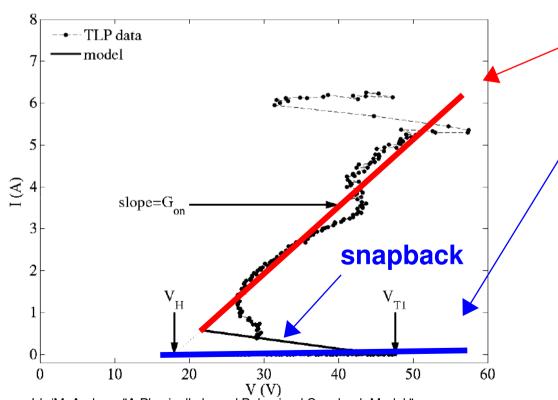


ESD Snapback Model

ESD protection device



Gendron, et al. "New High Voltage ESD Protection Devices based on Bipolar Transistors for Automotive Applications." IEEE EOS/ESD Symposium, 2011.



Ida/McAndrew. "A Physically-based Behavioral Snapback Model." IEEE EOS/ESD Symposium, 2012.

$$I_{on} = G_{on} \cdot (V - V_H)$$

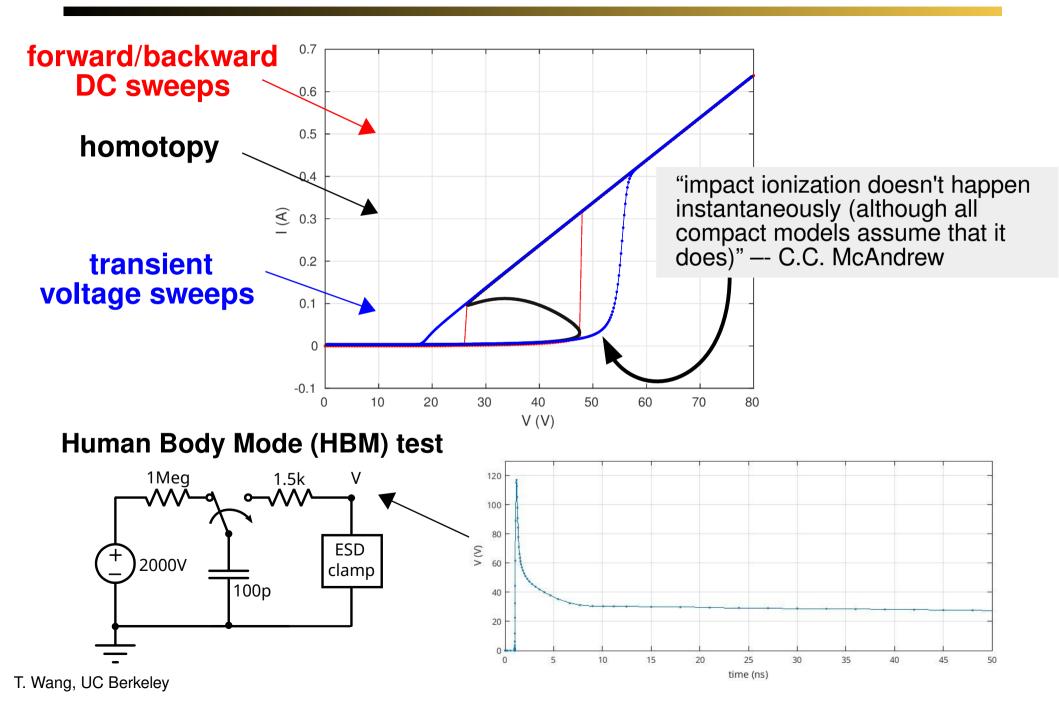
$$I_{off} = I_{S} \cdot (1 - e^{-V/\phi_{T}}) \cdot \sqrt{1 + \frac{max(V, 0)}{V_{D}}}$$

$$I = s \cdot I_{on} + I_{off}$$

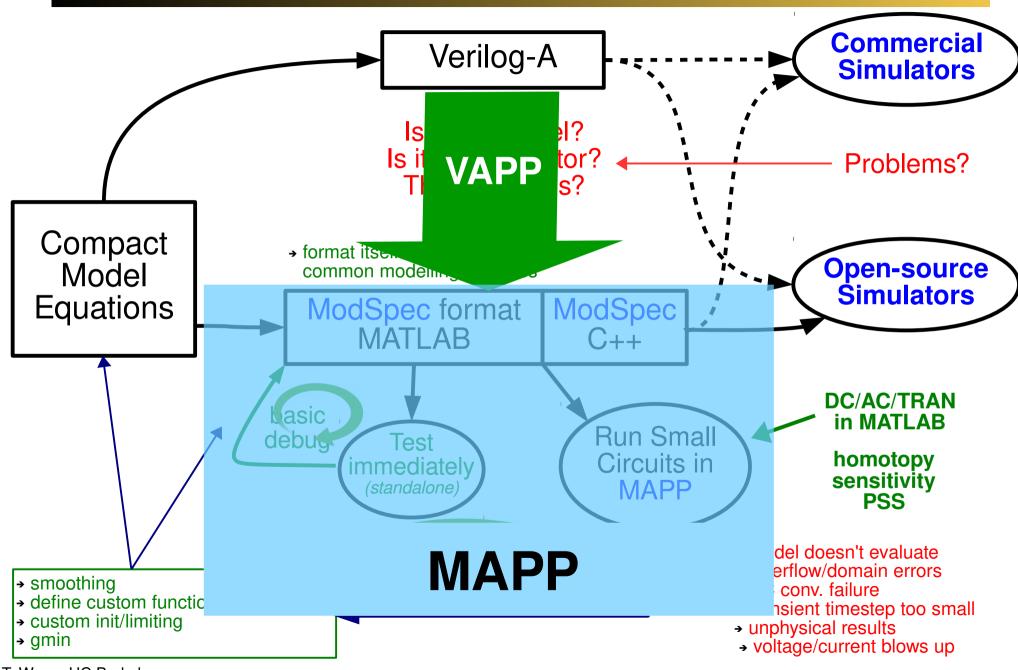
internal state: indicator of impact ionization

T. Wang, UC Berkeley

ESD Snapback Model



Compact Model Development



T. Wang, UC Berkeley